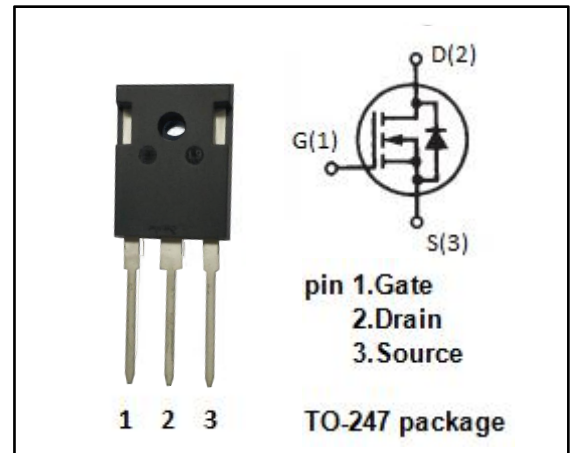


isc N-Channel MOSFET Transistor
R6524ENZ1
FEATURES

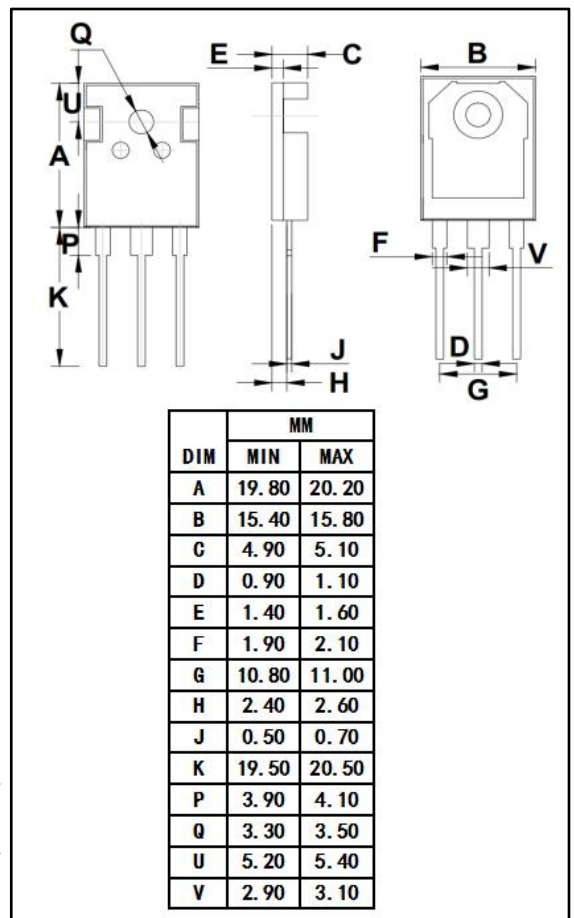
- Drain Current $-I_D = 24A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 650V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 185m\Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

- Designed for use in switch mode power supplies and general purpose applications.


ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|----------------------------------------|----------|------------|
| V_{DSS} | Drain-Source Voltage | 650 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 20 | V |
| I_D | Drain Current-Continuous | 24 | A |
| I_{DM} | Drain Current-Single Pluse | 72 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 245 | W |
| T_J | Max. Operating Junction Temperature | -55~150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |


THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|--------------------------------------|------|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 0.51 | $^\circ C/W$ |

isc N-Channel MOSFET Transistor

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|------------------------------------------------------------------------------------------------------------------|-----|-------------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 1mA | 650 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =750uA | 2 | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 11.3A | | 185 | mΩ |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±20V; V _{DS} = 0 | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 650V; V _{GS} = 0 V _{DS} = 650V; V _{GS} = 0@T _J =125°C | | 100 1000 | μA |
| V _{SD} | Forward On-Voltage | I _S = 24A; V _{GS} = 0 | | 1.5 | V |

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